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#10/Amend a
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8/9/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

N. Bojarczuk Jr., et al.

Serial No.: 10/059,422

Group Art Unit: 2814

Filed: January 31, 2002

Examiner: Theresa Doan

For: METHOD OF FORMING LATTICE-MATCHED STRUCTURE ON SILICON AND
STRUCTURE FORMED THEREBY

Honorable Assistant Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated March 31, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

FAX RECEIVED

JUL 31 2003

Please cancel withdrawn claims 1-14 and 28-55 without prejudice or disclaimer.

TECHNOLOGY CENTER 2800

1-14 (Withdrawn and canceled)

15. (Original) A semiconductor structure, comprising:

a substrate;

a crystalline oxide layer formed over said substrate; and

an epitaxial silicon layer formed on said crystalline oxide layer.

AI